



Final Product/Process Change Notification

Document #:FPCN25729XH

Issue Date:24 Feb 2025

Title of Change:	Dual Source Wafer Fab Strategy at LA Semiconductor and onsemi Bucheon, Korea for ESD and Surge Protection Products, and Datasheet Update.		
Proposed First Ship date:	31 May 2025 or earlier if approved by customer		
Contact Information:	Contact your local onsemi Sales Office.		
PCN Samples Contact:	Contact your local onsemi Sales Office. Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.		
Additional Reliability Data:	Contact your local onsemi Sales Office.		
Type of Notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. onsemi will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice.		
Marking of Parts/ Traceability of Change:	Changed material can be identified by lot code		
Change Category:	Wafer Fab Change		
Change Sub-Category(s):	Manufacturing Site Addition, Datasheet/Product Doc change		
Sites Affected:			
onsemi Sites		External Foundry/Subcon Sites	
onsemi Bucheon, Korea		None	
Description and Purpose:			
This Final notification (FPCN) is to advise customers of the dual source wafer fab strategy for the devices listed in the Affected Parts List.			
Upon implementation of this FPCN, parts can be sourced from either LA Semiconductor or onsemi Bucheon, Korea.			
	From	To	
Manufacturing location for Wafer Fab	LA Semiconductor, Idaho, United States	LA Semiconductor, Idaho, United States onsemi Bucheon, Korea	
The clamping voltage of 8/20 μ s waveform for all products listed in this FPCN will be revised as below.			
The datasheet will reflect the changes upon full customer approval.			
Test Item	Conditions	Current Max	New Max
Clamping Voltage (VC) (pulse width = 8/20 μ s)	IPP = 1 A, Any I/O to GND	8.5 V	9.0 V
	IPP = 5 A, Any I/O to GND	9.0 V	10.5 V
	IPP = 8 A, Any I/O to GND	10.0 V	11.5 V
	IPP = 25 A, Any I/O to GND	12.0 V	14.0 V
There is no product marking changes as a result of this change.			



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Reliability Data Summary:

QV DEVICE NAME: SZNSP4201MR6T1G

RMS: 97122

PACKAGE: TSOP6

Test	Specification	Condition	Interval	Results
High Temperature Reverse Bias	JESD22-A108	Ta=150°C, 100% max rated V	1008 hrs	0/ 231
High Temperature Storage Life	JESD22-A103	Ta=150°C	1008 hrs	0/ 231
Preconditioning	J-STD-020 JESD-A113	MSL 1 @260°C		0/693
Temperature Cycling	JESD22-A104	Ta= -65°C to +150°C	1000 cyc	0/ 231
Highly Accelerated Stress Test	JESD22-A110	130°C, 85% RH, 18.8psig, bias	96 hrs	0/ 231
Unbiased Highly Accelerated Stress Test	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/ 231

Electrical Characteristics Summary:

Limits have been changed per described in the details section for the part numbers listed in Affected Parts.

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the **PCN Customized Portal**.

Part Number	Qualification Vehicle
TVS4201MR6T1G	SZNSP4201MR6T1G
NSP2201MR6T1G	SZNSP4201MR6T1G
NSP4201MR6T1G	SZNSP4201MR6T1G